

# 54F/74F825 8-Bit D-Type Flip-Flop

# **General Description**

The 'F825 is an 8-bit buffered register. It has Clock Enable and Clear features which are ideal for parity bus interfacing in high performance microprogramming systems. Also included in the 'F825 are multiple enables that allow multiuser control of the interface.

The 'F825 is functionally and pin compatible with AMD's Am29825.

# **Features**

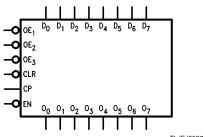
- TRI-STATE® output
- Clock enable and clear
- Multiple output enables
- Direct replacement for AMD's Am24825

Commercial	Military	Package Number	Package Description		
74F825SPC		N24C	24-Lead (0.300" Wide) Molded Dual-In-Line		
	54F825SDM (Note 2)	J24F	24-Lead (0.300" Wide) Ceramic Dual-In-Line		
74F825SC (Note 1)		M24B	24-Lead (0.300" Wide) Molded Small Outline, JEDEC		
	54F825FM (Note 2)	W24C	24-Lead Cerpack		
	54F825LM (Note 2)	E28A	24-Lead Ceramic Leadless Chip Carrier, Type C		

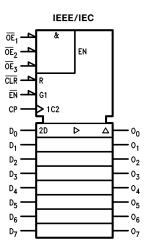
Note 1: Devices also available in 13" reel. Use suffix = SCX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = SDMQB, FMQB and LMQB.

## **Logic Symbols**



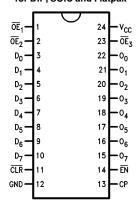
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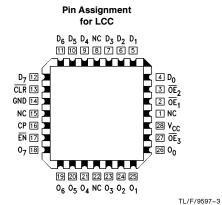


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# **Connection Diagrams**

Pin Assignment for DIP, SOIC and Flatpak





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# **Unit Loading/Fan Out**

		54F/74F				
Pin Names	Description	U.L. HIGH/LOW	Input I <sub>IH</sub> /I <sub>IL</sub> Output I <sub>OH</sub> /I <sub>OL</sub>			
D <sub>0</sub> -D <sub>7</sub>	Data Inputs	1.0/1.0	20 μA/-0.6 mA			
O <sub>0</sub> -O <sub>7</sub>	TRI-STATE Data Outputs	150/40 (33.3)	-3 mA/24 mA (20 mA)			
$\overline{OE}_1$ , $\overline{OE}_2$ , $\overline{OE}_3$	Output Enable Input	1.0/1.0	20 μA/-0.6 mA			
EN	Clock Enable	1.0/1.0	20 μA/ – 0.6 mA			
CLR	Clear	1.0/1.0	20 μA/ – 0.6 mA			
СР	Clock Input	1.0/2.0	20 μA/ – 1.2 mA			

## **Functional Description**

The 'F825 consists of eight D-type edge-triggered flip-flops. This device has TRI-STATE true outputs and is organized in broadside pinning. In addition to the clock and output enable pins, the buffered clock (CP) and buffered Output En able  $(\overline{\text{OE}})$  are common to all flip-flops. The flip-flops will store the state of their individual D inputs that meet the setup and hold times requirements on the LOW-to-HIGH CP transition. With the  $\overline{\text{OE}}$  LOW the contents of the flip-flops are available at the outputs. When the  $\overline{\text{OE}}$  is HIGH, the outputs go to the high impedance state. Operation of the  $\overline{\text{OE}}$ 

input does not affect the state of the flip-flops. The 'F825 has Clear (CLR) and Clock Enable (EN) pins.

When the  $\overline{\text{CLR}}$  is LOW and the  $\overline{\text{OE}}$  is LOW the outputs are LOW. When CLR is HIGH, data can be entered into the flipflops. When  $\overline{\mathsf{EN}}$  is LOW, data on the inputs is transferred to the outputs on the LOW-to-HIGH clock transition. When the EN is HIGH the outputs do not change state, regardless of the data or clock input transitions.

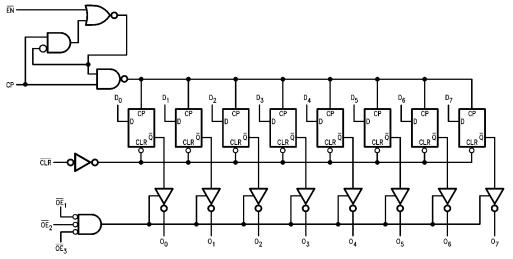
**Function Table** 

Inputs			Internal	Output	Function		
ŌĒ	CLR	ĒΝ	СР	D	Q	0	Tunction
Н	Н	L	Н	Х	NC	Z	Hold
Н	Н	L	L	Χ	NC	Z	Hold
Н	Н	Н	Χ	X	NC	Z	Hold
L	Н	Н	Χ	Χ	NC	NC	Hold
Н	L	Χ	Χ	X	Н	Z	Clear
L	L	Χ	Χ	X	Н	L	Clear
Н	Н	L	$\mathcal{L}$	L	Н	Z	Load
Н	Н	L	$\mathcal{L}$	Н	L	Z	Load
L	Н	L	_	L	Н	L	Data Available
L	Н	L	_	Н	L	Н	Data Available
L	Н	L	Н	Χ	NC	NC	No Change in Data
L	Н	L	L	X	NC	NC	No Change in Data

- $\begin{array}{l} \mathsf{L} = \mathsf{LOW} \; \mathsf{Voltage} \; \mathsf{Level} \\ \mathsf{H} = \mathsf{HIGH} \; \mathsf{Voltage} \; \mathsf{Level} \\ \mathsf{X} = \mathsf{Immaterial} \end{array}$

- High Impedance= LOW-to-HIGH Transition
- NC = No Change

## **Logic Diagram**



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Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

#### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature -65°C to +150°C

Ambient Temperature under Bias

Junction Temperature under Bias

Plastic

Plastic

-65°C to +150°C

-55°C to +175°C

-55°C to +150°C

V<sub>CC</sub> Pin Potential to

Ground Pin −0.5V to +7.0V
Input Voltage (Note 2) −0.5V to +7.0V

Input Current (Note 2)  $$-30\ \text{mA}$\ \text{to}$\ +5.0\ \text{mA}$$ 

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

 $\begin{array}{lll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$ 

Current Applied to Output in LOW State (Max)

twice the rated  $I_{OL}$  (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

# Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military +4.5V to +5.5V Commercial +4.5V to +5.5V

#### **DC Electrical Characteristics**

Symbol	Parameter		54F/74F			Units	V <sub>CC</sub>	Conditions	
Symbol	Faranie	raiailietei –		Тур	Max	Omis	▼CC	Conditions	
V <sub>IH</sub>	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
V <sub>IL</sub>	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
V <sub>CD</sub>	Input Clamp Diode Voltage				-1.2	V	Min	$I_{\text{IN}} = -18  \text{mA}$	
V <sub>OH</sub>	Output HIGH Voltage	54F 10% V <sub>CC</sub> 54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 5% V <sub>CC</sub> 74F 5% V <sub>CC</sub>	2.5 2.4 2.5 2.4 2.7 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub>			0.5 0.5	٧	Min	I <sub>OL</sub> = 20 mA I <sub>OL</sub> = 24 mA	
I <sub>IH</sub>	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{\text{IN}} = 2.7V$	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V <sub>IN</sub> = 7.0V	
I <sub>CEX</sub>	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
$V_{ID}$	Input Leakage Test	74F	4.75			V	0.0	$I_{ m ID}=1.9~\mu{ m A}$ All Other Pins Grounded	
I <sub>OD</sub>	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All Other Pins Grounded	
I <sub>IL</sub>	Input LOW Current				-0.6	mA	Max	V <sub>IN</sub> = 0.5V	
lozh	Output Leakage Current				50	μΑ	Max	V <sub>OUT</sub> = 2.7V	
l <sub>OZL</sub>	Output Leakage Current				-50	μΑ	Max	V <sub>OUT</sub> = 0.5V	
I <sub>OS</sub>	Output Short-Circuit Current		-60		-150	mA	Max	V <sub>OUT</sub> = 0V	
I <sub>ZZ</sub>	Buss Drainage Test				500	μΑ	0.0V	V <sub>OUT</sub> = 5.25V	
Iccz	Power Supply Curren	t		75	90	mA	Max	V <sub>O</sub> = HIGH Z	

## **AC Electrical Characteristics**

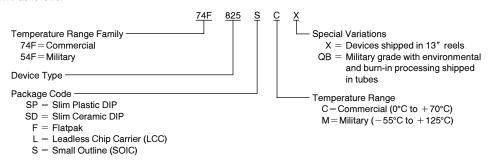
		$74F$ $T_{A} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$			54F  T <sub>A</sub> , V <sub>CC</sub> = Mil  C <sub>L</sub> = 50 pF		74F  T <sub>A</sub> , V <sub>CC</sub> = Com C <sub>L</sub> = 50 pF		Units
Symbol	Parameter								
		Min	Тур	Max	Min	Max	Min	Max	
f <sub>max</sub>	Maximum Clock Frequency	100	160		60		70		MHz
t <sub>PLH</sub>	Propagation Delay CP to O <sub>n</sub>	2.0 2.0	6.5 6.6	9.5 9.5	2.0 2.0	10.5 10.5	2.0 2.0	10.5 10.5	ns
t <sub>PHL</sub>	Propagation Delay CLR to O <sub>n</sub>	4.0	7.4	12.0	4.0	13.0	4.0	13.0	ns
t <sub>PZH</sub>	Output Enable Time OE to On	2.0 2.0	6.5 6.6	10.5 10.5	2.0 2.0	13.0 13.0	2.0 2.0	11.5 11.5	- ns
t <sub>PHZ</sub>	Output Disable TIme OE to O <sub>n</sub>	1.5 1.5	3.5 3.3	7.0 7.0	1.0 1.0	7.5 7.5	1.5 1.5	7.5 7.5	

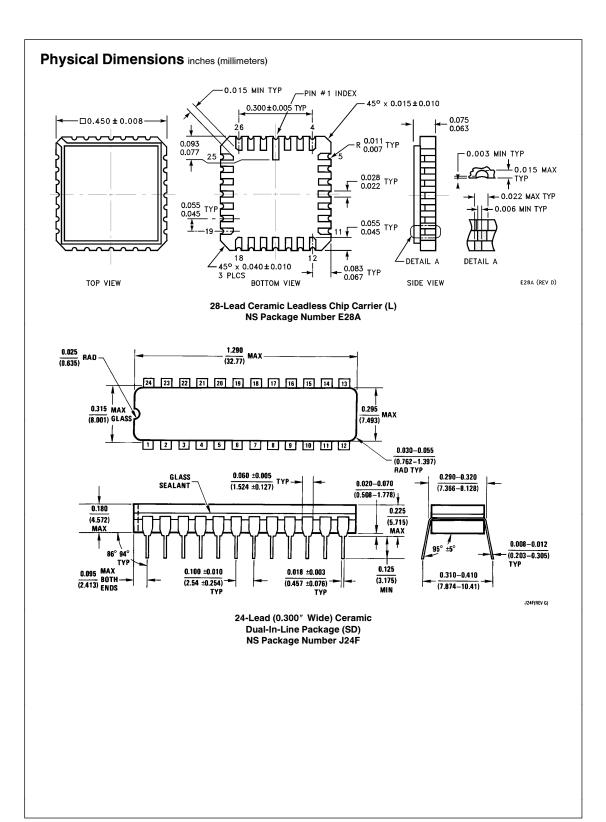
# **AC Operating Requirements**

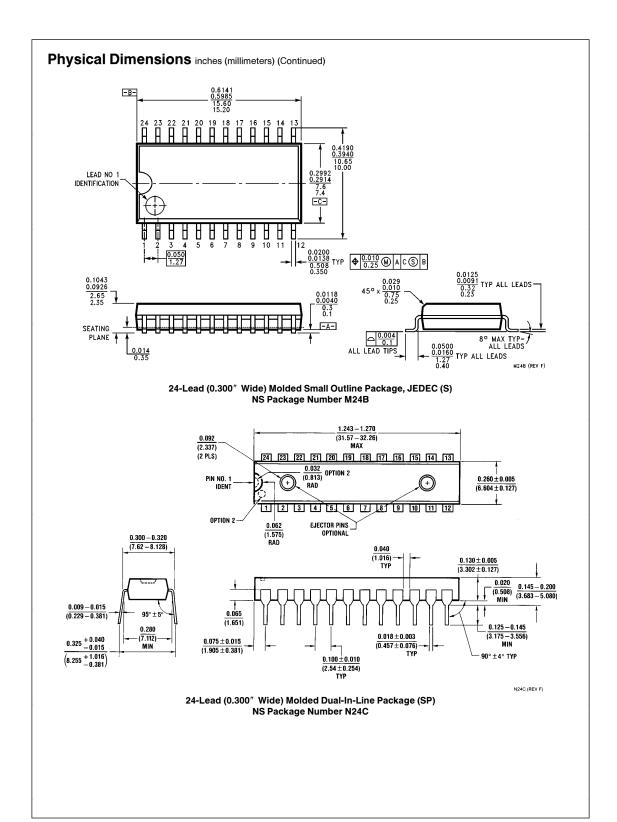
		$74F$ $T_A = +25^{\circ}C$ $V_{CC} = +5.0V$		54	F	74F  T <sub>A</sub> , V <sub>CC</sub> = Com		Units
Symbol	Parameter			T <sub>A</sub> , V <sub>CC</sub>	; = Mil			
		Min	Max	Min	Max	Min	Max	
t <sub>s</sub> (H) t <sub>s</sub> (L)	Setup Time, HIGH or LOW D <sub>n</sub> to CP	2.5 2.5		4.0 4.0		3.0 3.0		ns
t <sub>h</sub> (H)	Hold Time, HIGH or LOW D <sub>n</sub> to CP	2.5 2.5		2.5 2.5		2.5 2.5		113
t <sub>s</sub> (H)	Setup Time, HIGH or LOW EN to CP	4.5 2.5		5.0 3.0		5.0 3.0		ns
t <sub>h</sub> (H)	Hold Time, HIGH or LOW EN to CP	2.0 0		3.0 2.0		1.0 0		113
t <sub>w</sub> (H)	CP Pulse Width HIGH or LOW	5.0 5.0		6.0 6.0		6.0 6.0		ns
t <sub>w</sub> (L)	CLR Pulse Width, LOW	5.0		5.0		5.0		ns
t <sub>rec</sub>	CLR Recovery Time	5.0		5.0		5.0		ns

## **Ordering Information**

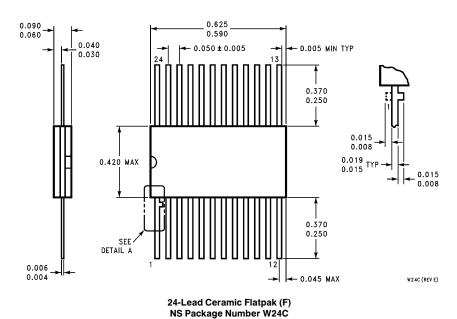
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:







# Physical Dimensions inches (millimeters) (Continued)



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